

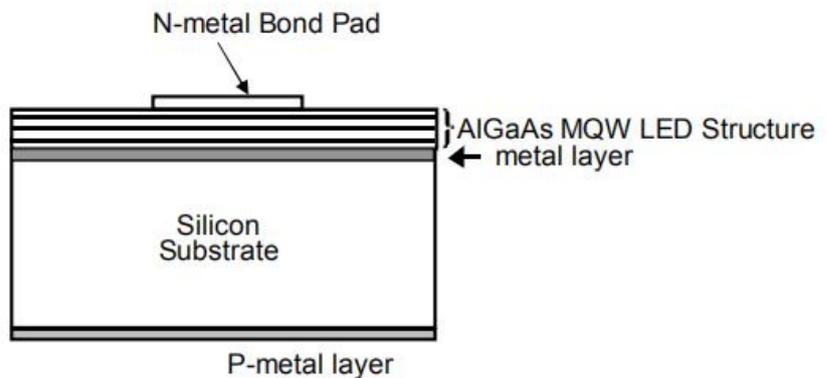
IN-F26IR-D

Great Performances:

- Larger Emitting Area
- 100% Tested & Sorted
- Conductive Si-substrate
- Outdoor Applications
- Rough Surface

Descriptions:

F26IR is a Infra-red LED chip made from MOCVD process and bonded with Silicon. It is fabricated by the proprietary metal Bonding mechanism, F26IR is featured by homogeneous and high light output at top side with superior beam pattern. Excellent performance under sunlight and reliable life-long stability make F26IR ideal for IrDA, Encoder, data communication applications.



Chip Dimension

1. Chip size: $620 \pm 25\mu\text{m} \times 620 \pm 25\mu\text{m}$
2. Chip thickness: $180 \pm 15\mu\text{m}$
3. N-bonding pad: Au pad $\phi 104 \pm 15\mu\text{m}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V_{F1}	1.3	1.5	1.8	V	$I_F=150\text{ mA}$
Threshold Voltage	V_{F3}	1.0	-	1.3	V	$I_F=10\ \mu\text{A}$
Reverse Current	I_R	-	-	10.0	μA	$V_R=5\text{ V}$
Peak Wavelength	λ_p	800	-	900	nm	$I_F=150\text{ mA}$
Spectral Line Half Width	$\Delta\lambda$	-	30	-	nm	$I_F=150\text{ mA}$
Radiation Power	P_o	25	-	-	mW	$I_F=150\text{ mA}$

* P_o is measured on chip form with HPO's tester.